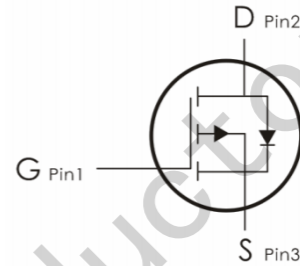
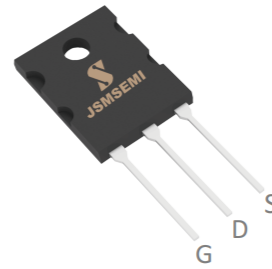


## FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
IXTK110N20L2	TO-264	IXTK110N20L2

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted			
Parameter	Symbol	Value	Unit
		TO-264	
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	200	V
Continuous Drain Current $V_{GS} = 10\text{V}$ $T_C = 25^\circ\text{C}$	$I_b$	110	A
Pulsed Drain Current (note1)	$I_{DM}$	440	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	1960.2	mJ
Avalanche Current (note1)	$I_{AS}$	19.8	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	1176.1	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	900	W
Peak Diode Recovery dv/dt (note1)	dv/dt	5.0	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.89	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	60	

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 32V, V_{GS} = 0V, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 60A$	--	20	25	m $\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	5784	--	pF
Output Capacitance	$C_{oss}$		--	893	--	
Reverse Transfer Capacitance	$C_{rss}$		--	561	--	
Total Gate Charge	$Q_g$	$V_{DD} = 20V, I_D = 190A,$ $V_{GS} = 10V$	--	367	--	nC
Gate-Source Charge	$Q_{gs}$		--	33.8	--	
Gate-Drain Charge	$Q_{gd}$		--	177	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 20V, I_D = 190A,$ $R_G = 10\Omega, V_{GS} = 10V$	--	55	--	ns
Turn-on Rise Time	$t_r$		--	165	--	
Turn-off Delay Time	$t_{d(off)}$		--	1050	--	
Turn-off Fall Time	$t_f$		--	367	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	110	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	440	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 95A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 190A,$ $di_F/dt = 100A/\mu s$	--	360	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	5.61	--	$\mu C$

**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 10\text{mH}, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )

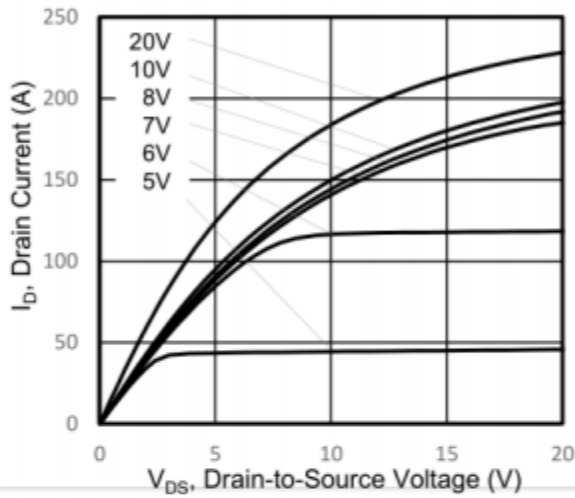


Figure 2. Body Diode Forward Voltage

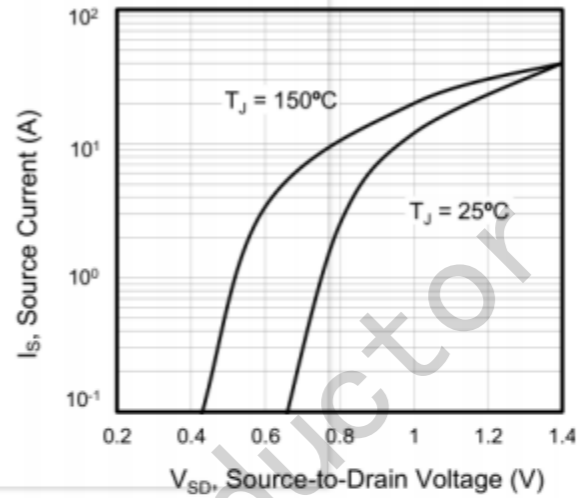


Figure 3. Drain Current vs. Temperature

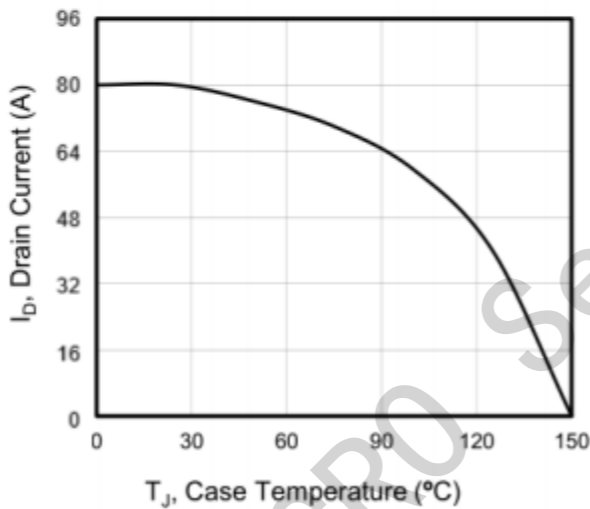


Figure 4.  $BV_{DSS}$  Variation vs. Temperature

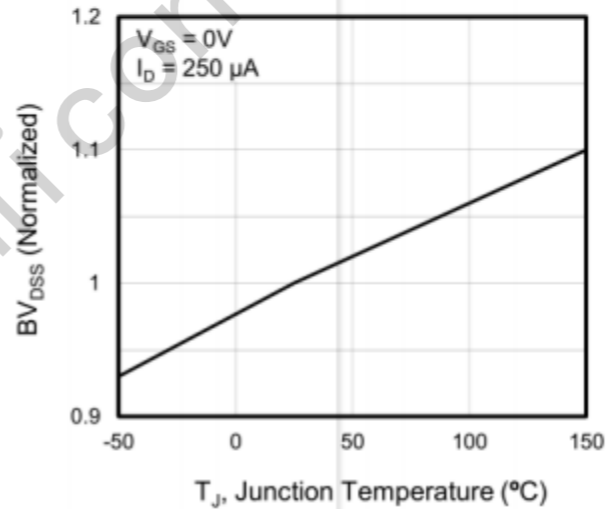


Figure 5. Transfer Characteristics

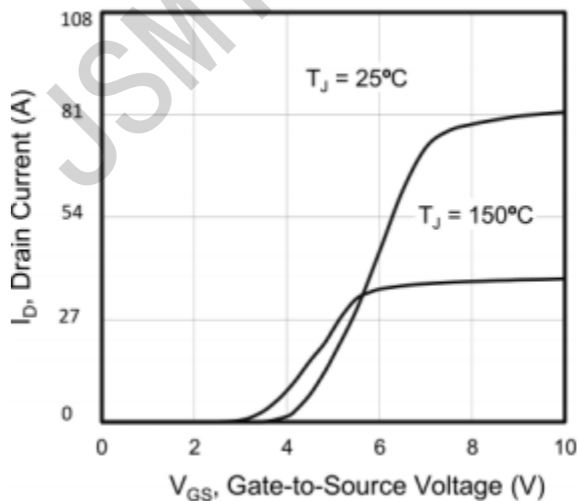
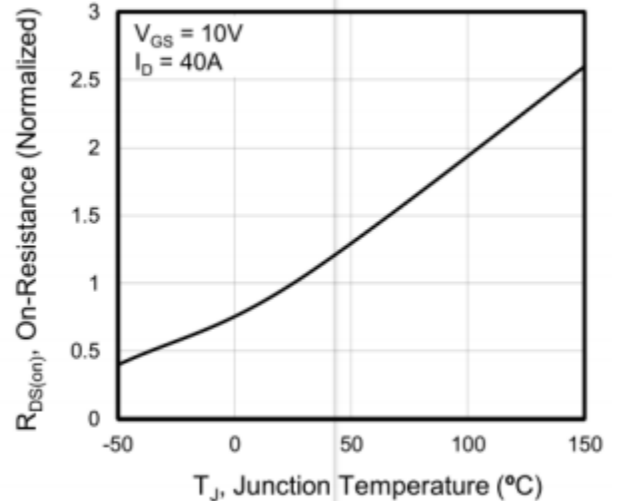


Figure 6. On-Resistance vs. Temperature



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

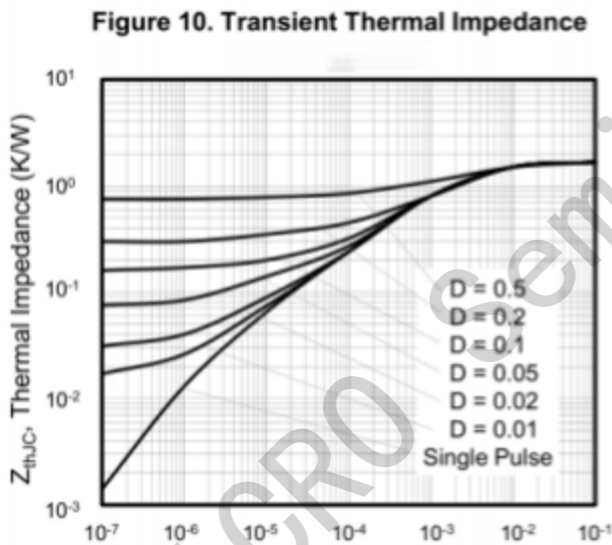
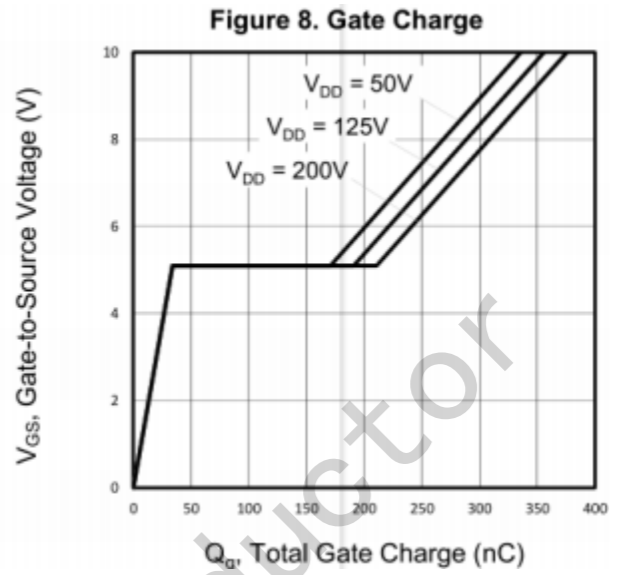
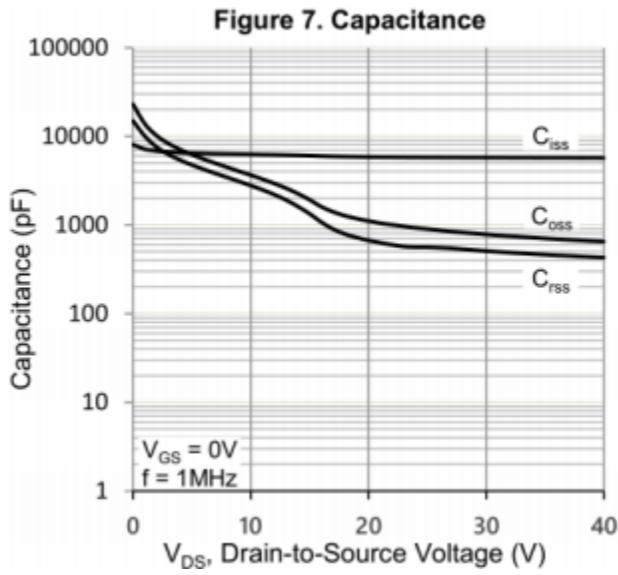


Figure A: Gate Charge Test Circuit and Waveform

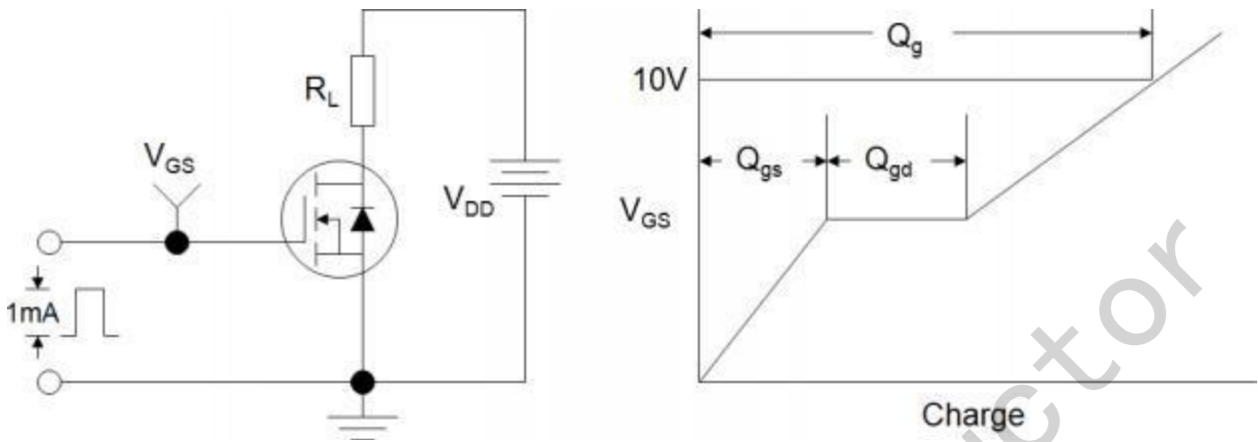


Figure B : Resistive Switching Test Circuit and Waveform

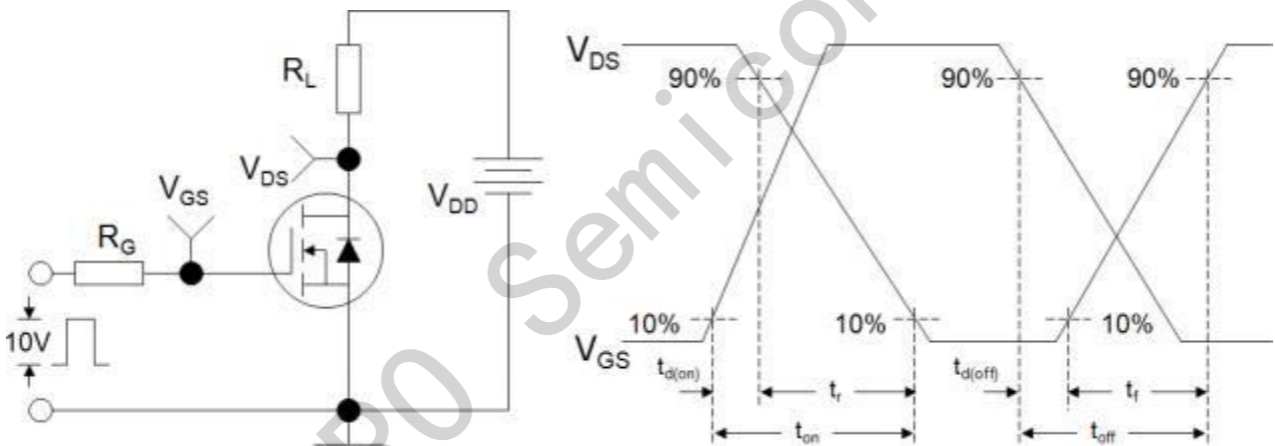
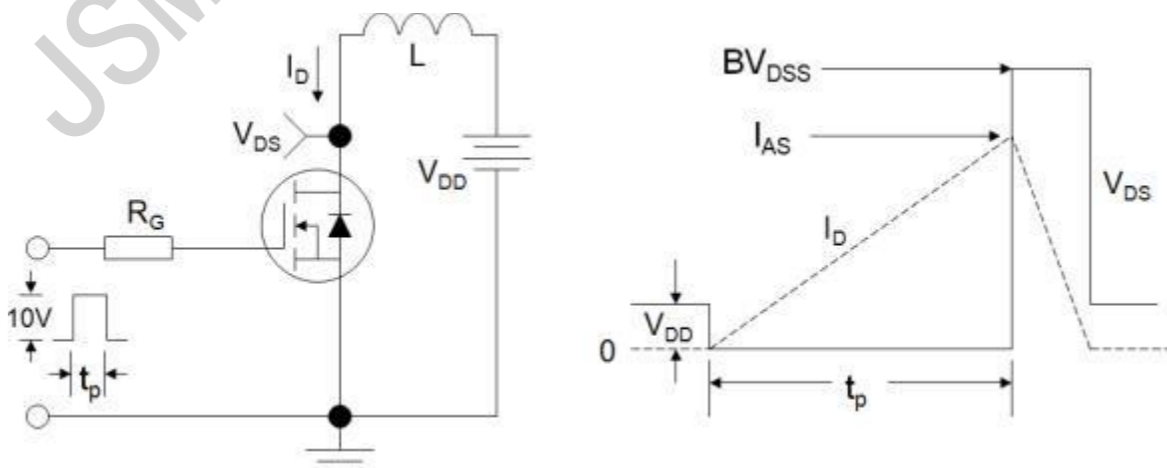


Figure C : Unclamped Inductive Switching Test Circuit and Waveform



TO-264 Package Dimensions

